

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C
-30V	50mΩ @ V _{GS} = -10V	-4.5A
	75mΩ @ V _{GS} = -4.5V	-3.7A

Features

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **The DMP3050LVTQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF16949 certified facilities.**

<https://www.diodes.com/quality/product-definitions/>

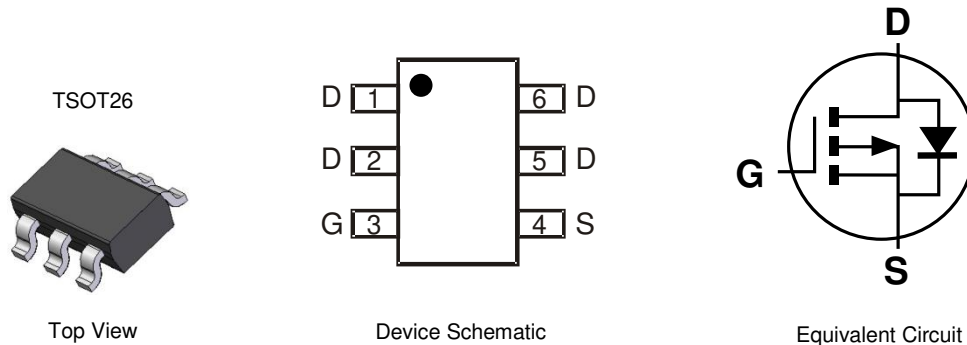
Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Backlighting
- Power management functions
- DC-DC converters

Mechanical Data

- Package: TSOT26
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish — Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (E3)
- Weight: 0.013grams (Approximate)

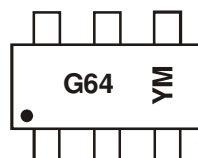


Ordering Information (Note 4)

Part Number	Package	Packing	
		Qty.	Carrier
DMP3050LVTQ-7	TSOT26	3000	Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



G64 = Product Type Marking Code
 YM = Date Code Marking
 Y or \bar{Y} = Year (ex: J = 2022)
 M = Month (ex: 1 = January)

Date Code Key

Year	2019	2020	2021	2022	2023	2024	2025	2026	2027	2028	2029	2030
Code	G	H	I	J	K	L	M	N	O	P	R	S

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	-30	V
Gate-Source Voltage (Note 5)			V _{GSS}	±25	V
Continuous Drain Current (Note 6) V _{GS} = -10V	Steady State	T _A = +25°C	I _D	-4.5	A
		T _A = +70°C		-3.5	
	t < 10s	T _A = +25°C	I _D	-5.2	A
		T _A = +70°C		-4.1	
Maximum Continuous Body Diode Forward Current (Note 6)			I _S	-2	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I _{DM}	-25	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 6)	T _A = +25°C	P _D	1.6	W
	T _A = +70°C		1.0	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R _{θJA}	78	°C/W
	t < 10s		49	
Thermal Resistance, Junction to Case (Note 6)	Steady State	R _{θJC}	13	
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	-30	—	—	V	V _{GS} = 0V, I _D = -250µA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	-1	µA	V _{DS} = -30V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	-1.0	—	-2.0	V	V _{DS} = V _{GS} , I _D = -250µA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	36	50	mΩ	V _{GS} = -10V, I _D = -4.5A
		—	56	75		V _{GS} = -4.5V, I _D = -3A
Forward Transfer Admittance	Y _{fs}	—	7.2	—	s	V _{DS} = -5V, I _D = -5A
Diode Forward Voltage	V _{SD}	—	-0.7	-1.0	V	V _{GS} = 0V, I _S = -1A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	—	620	—	pF	V _{DS} = -15V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	—	83	—	pF	
Reverse Transfer Capacitance	C _{rss}	—	62	—	pF	
Gate Resistance	R _g	—	10.8	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz
Total Gate Charge (V _{GS} = -4.5V)	Q _g	—	5.1	—	nC	V _{DS} = -15V, I _D = -6A
Total Gate Charge (V _{GS} = -10V)	Q _g	—	10.5	—	nC	
Gate-Source Charge	Q _{gs}	—	1.8	—	nC	
Gate-Drain Charge	Q _{gd}	—	1.9	—	nC	
Turn-On Delay Time	t _{D(ON)}	—	6.8	—	ns	V _{DD} = -15V, V _{GS} = -10V, R _g = 6Ω, I _D = -1A
Turn-On Rise Time	t _R	—	4.9	—	ns	
Turn-Off Delay Time	t _{D(OFF)}	—	28.4	—	ns	
Turn-Off Fall Time	t _F	—	12.4	—	ns	

- Notes:
- AEC-Q101 V_{GS} maximum is ±20V.
 - Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

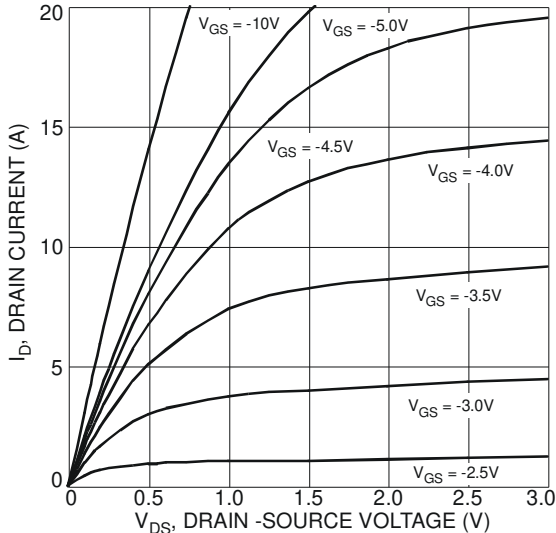


Fig. 1 Typical Output Characteristics

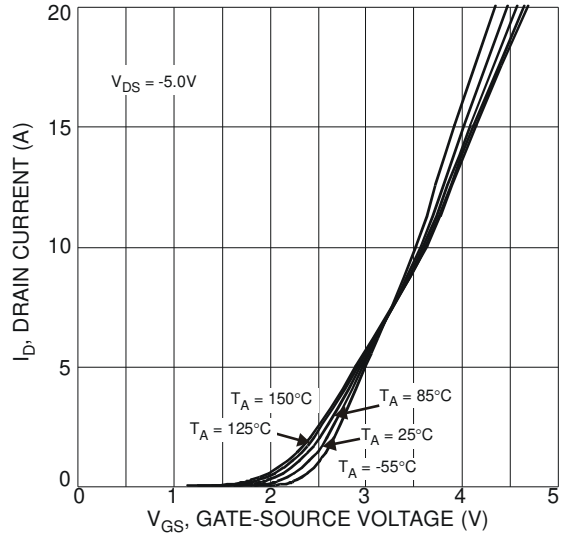


Fig. 2 Typical Transfer Characteristics

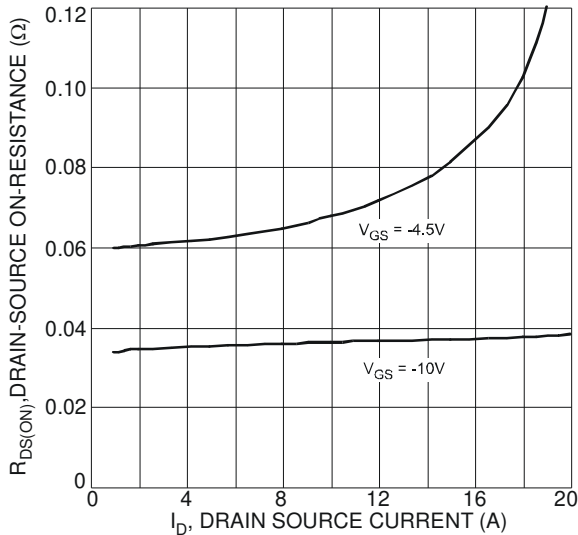


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

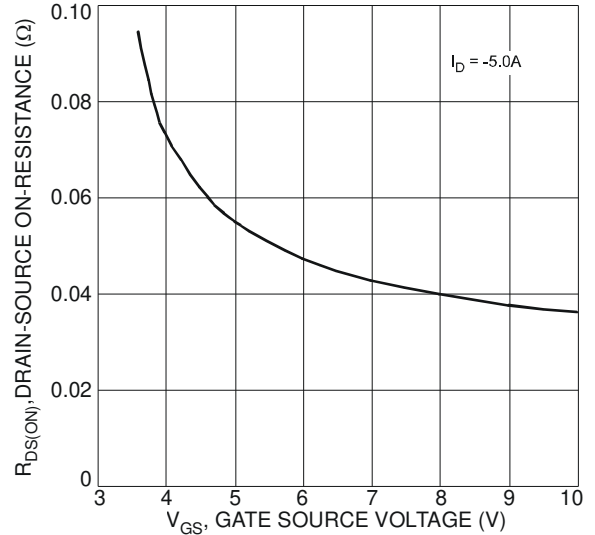


Fig. 4 Typical On-Resistance vs. Drain Current and Gate Voltage

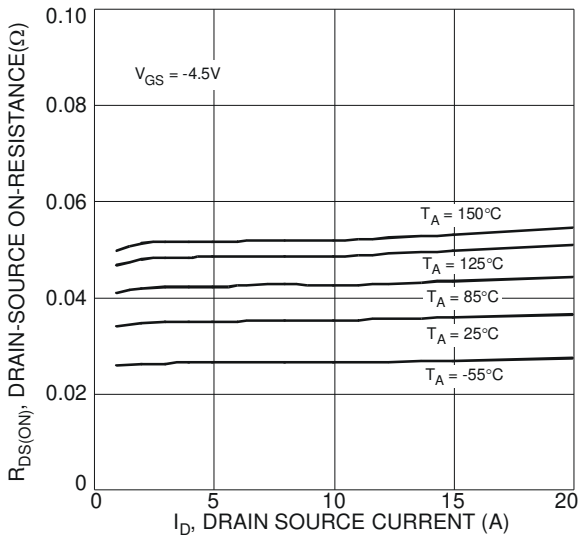


Fig. 5 Typical On-Resistance vs. Drain Current and Temperature

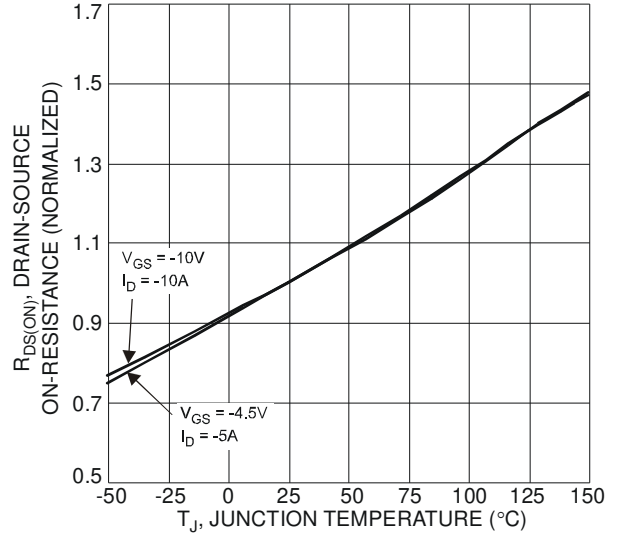


Fig. 6 On-Resistance Variation with Temperature

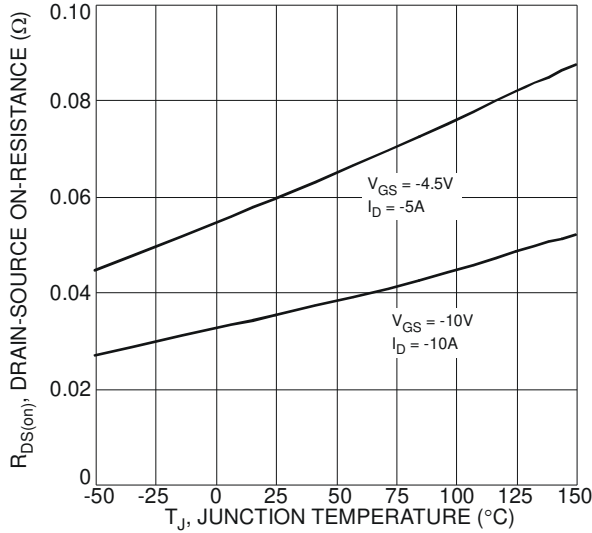


Fig. 7 On-Resistance Variation with Temperature

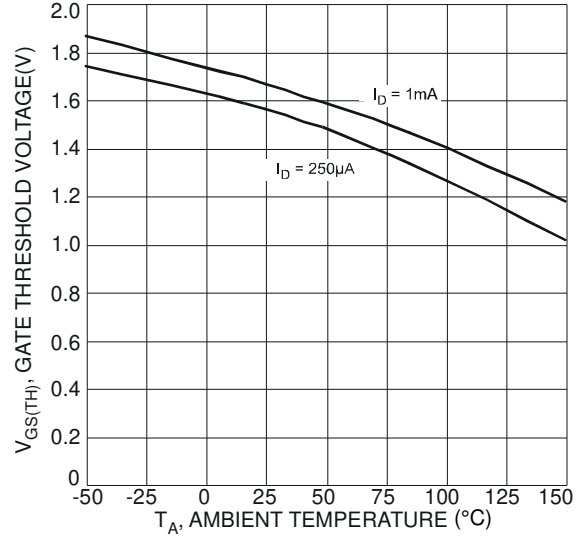


Fig. 8 Gate Threshold Variation vs. Ambient Temperature

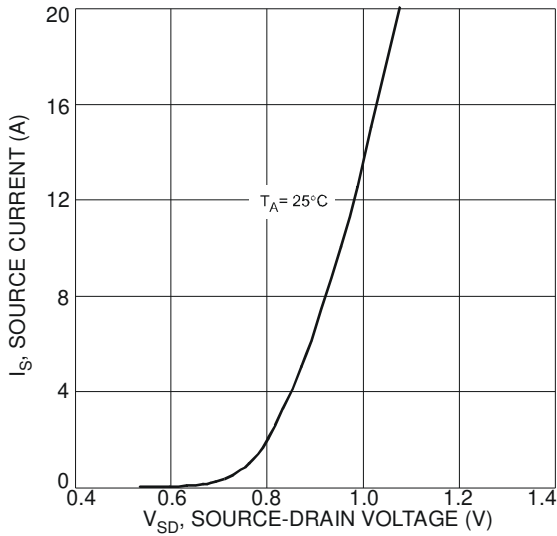


Fig. 9 Diode Forward Voltage vs. Current

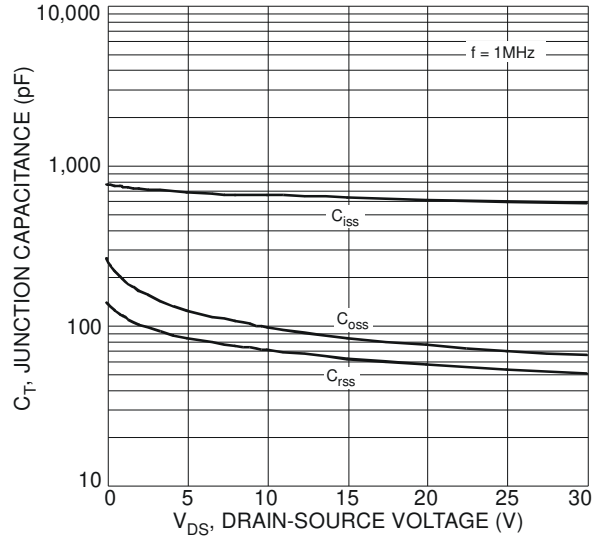


Fig. 10 Typical Junction Capacitance

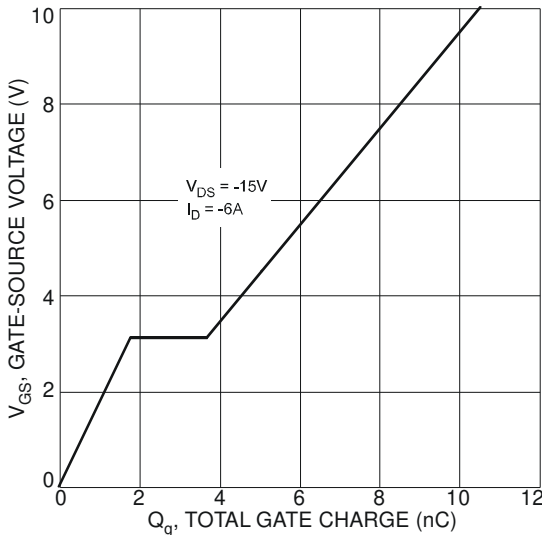


Fig. 11 Gate-Charge Characteristics

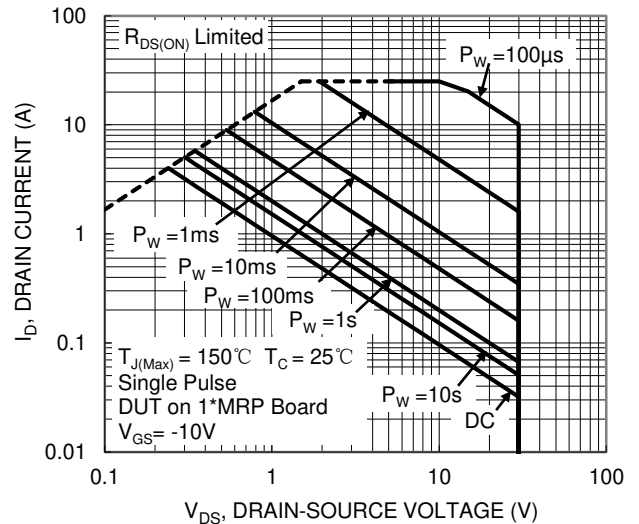


Fig. 12 SOA, Safe Operation Area

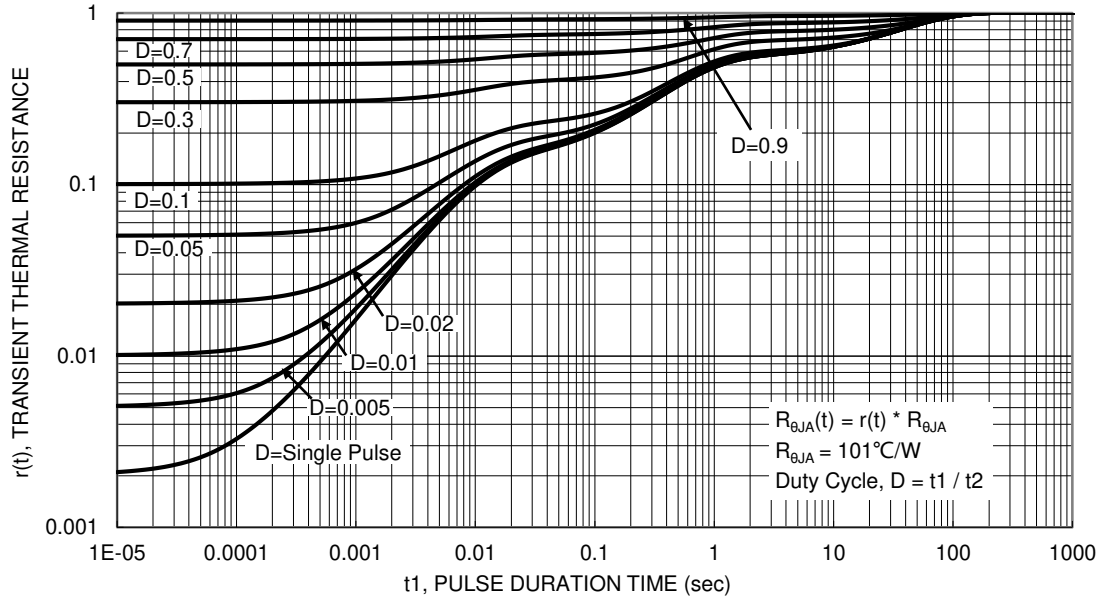
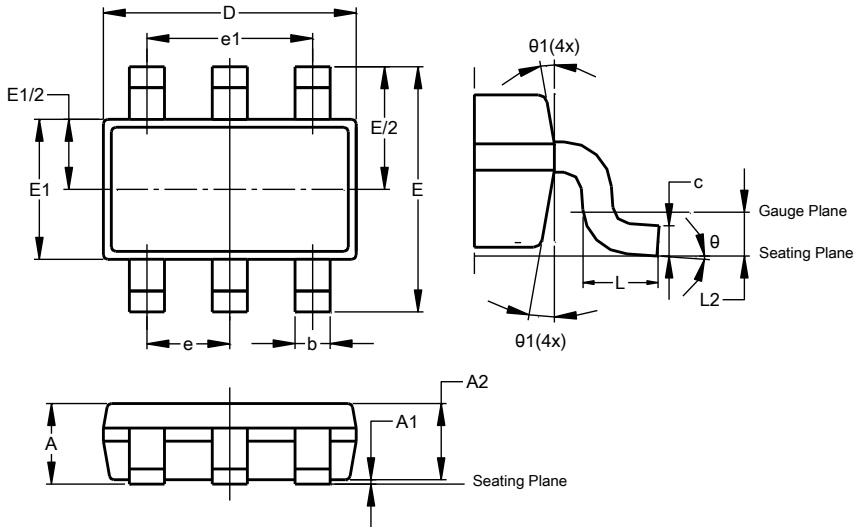


Fig. 13 Transient Thermal Resistance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

TSOT26

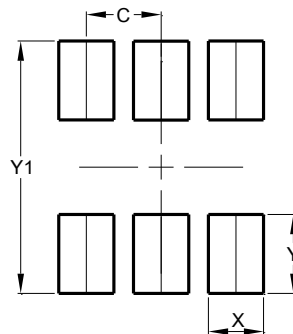


TSOT26			
Dim	Min	Max	Typ
A	–	1.00	–
A1	0.010	0.100	–
A2	0.840	0.900	–
D	2.800	3.000	2.900
E	2.800 BSC		
E1	1.500	1.700	1.600
b	0.300	0.450	–
c	0.120	0.200	–
e	0.950 BSC		
e1	1.900 BSC		
L	0.30	0.50	–
L2	0.250 BSC		
θ	0°	8°	4°
θ1	4°	12°	–
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

TSOT26



Dimensions	Value (in mm)
C	0.950
X	0.700
Y	1.000
Y1	3.200

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